

## Product Summary

| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ max}$      | $I_D \text{ max}$<br>$T_A = +25^\circ\text{C}$ |
|---------------|-------------------------------|------------------------------------------------|
| 40V           | 7.5mΩ @ $V_{GS} = 10\text{V}$ | 14.4A                                          |
|               | 10mΩ @ $V_{GS} = 4.5\text{V}$ | 12.5A                                          |

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

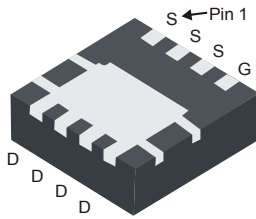
## Features and Benefits

- Low  $R_{DS(ON)}$  – ensures on state losses are minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

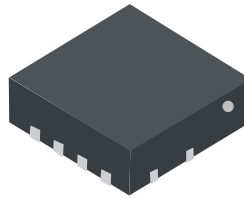
## Mechanical Data

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.072 grams (approximate)

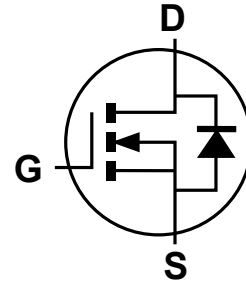
POWERDI®3333-8



Bottom View



Top View



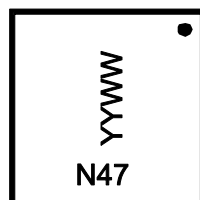
Equivalent Circuit

## Ordering Information (Note 4)

| Part Number   | Case           | Packaging        |
|---------------|----------------|------------------|
| DMN4008LFG-7  | POWERDI®3333-8 | 2000/Tape & Reel |
| DMN4008LFG-13 | POWERDI®3333-8 | 3000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



N47= Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last digit of year (ex: 13 = 2013)  
WW = Week code (01 ~ 53)

| Characteristic                                          |              |                        | Symbol           | Value | Units |
|---------------------------------------------------------|--------------|------------------------|------------------|-------|-------|
| Drain-Source Voltage                                    |              |                        | V <sub>DSS</sub> | 40    | V     |
| Gate-Source Voltage                                     |              |                        | V <sub>GSS</sub> | ±20   | V     |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V | Steady State | T <sub>A</sub> = +25°C | I <sub>D</sub>   | 14.4  | A     |
|                                                         |              | T <sub>A</sub> = +70°C | I <sub>D</sub>   | 11.6  | A     |
|                                                         | t < 10s      | T <sub>A</sub> = +25°C | I <sub>D</sub>   | 19.2  | A     |
|                                                         |              |                        | I <sub>D</sub>   | 15.4  | A     |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%)      |              |                        | I <sub>DM</sub>  | 90    | A     |
| Maximum Continuous Body Diode Forward Current (Note 6)  |              |                        | I <sub>S</sub>   | 3     | A     |
| Avalanche Current, L = 0.1mH                            |              |                        | I <sub>AS</sub>  | 38    | A     |
| Avalanche Energy, L = 0.1mH                             |              |                        | E <sub>AS</sub>  | 75    | mJ    |

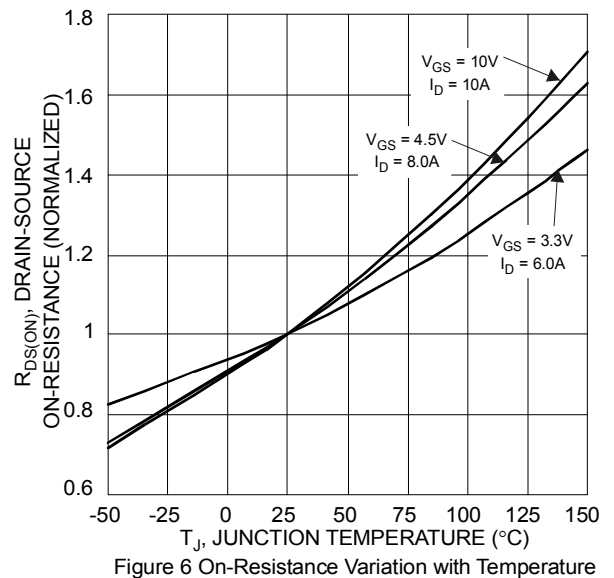
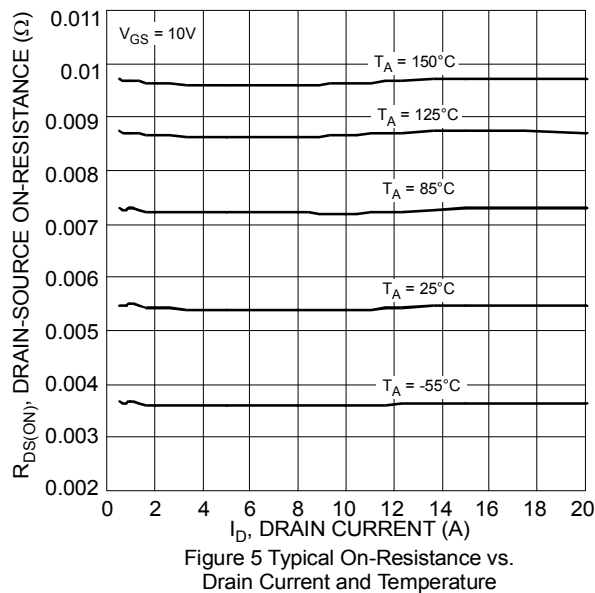
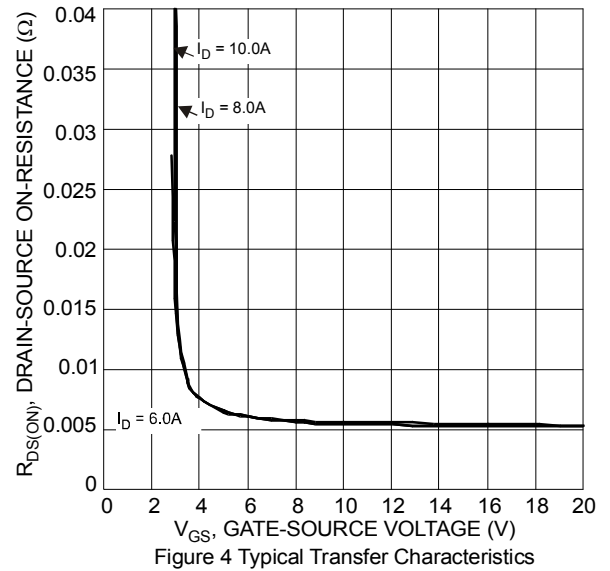
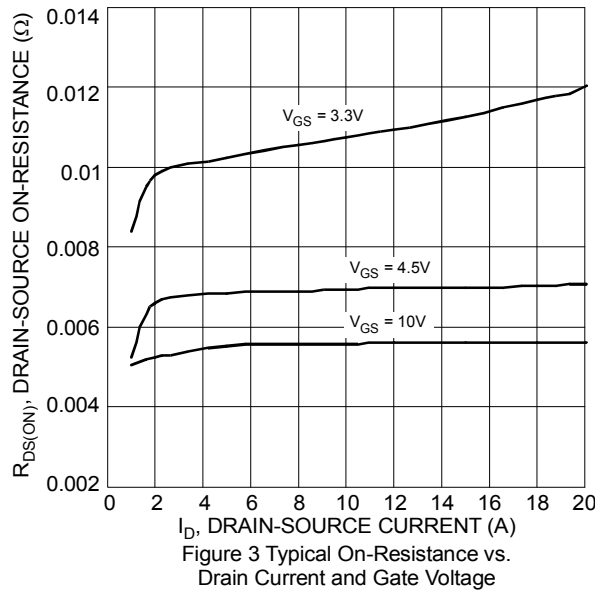
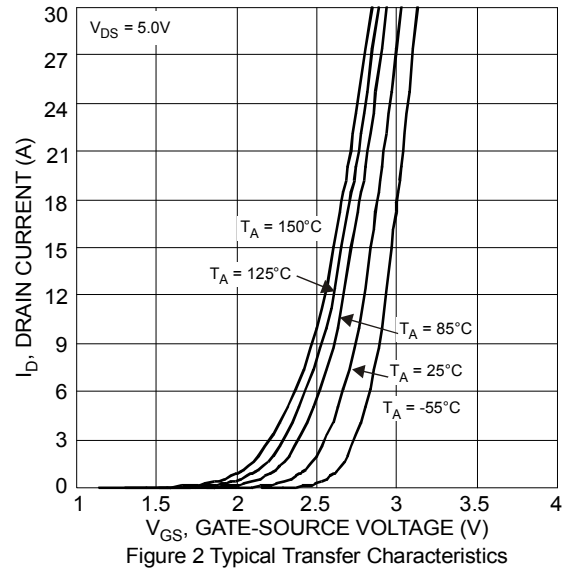
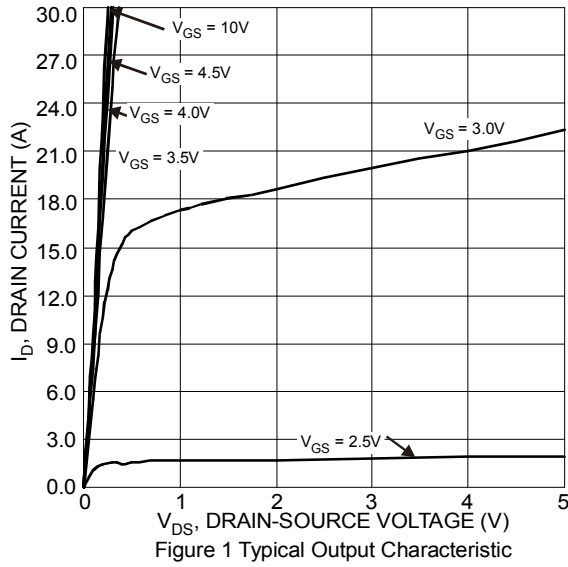
## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

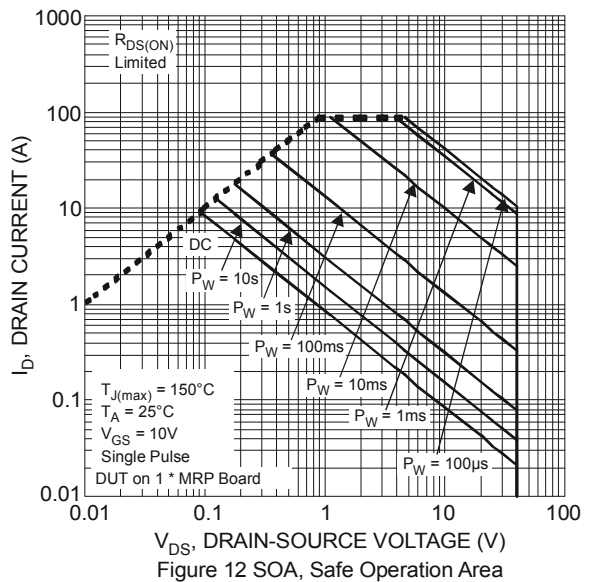
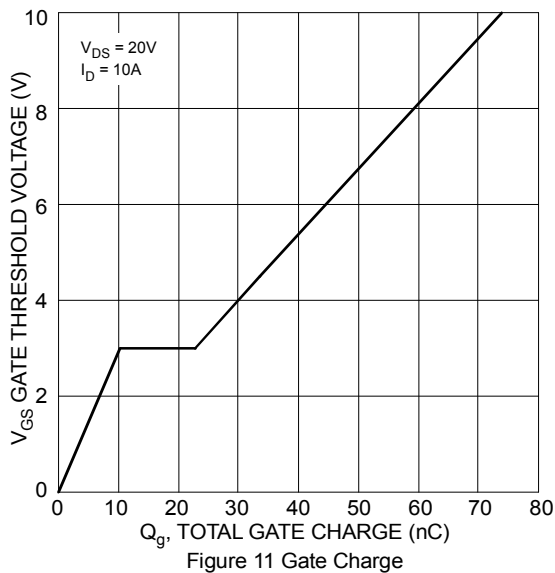
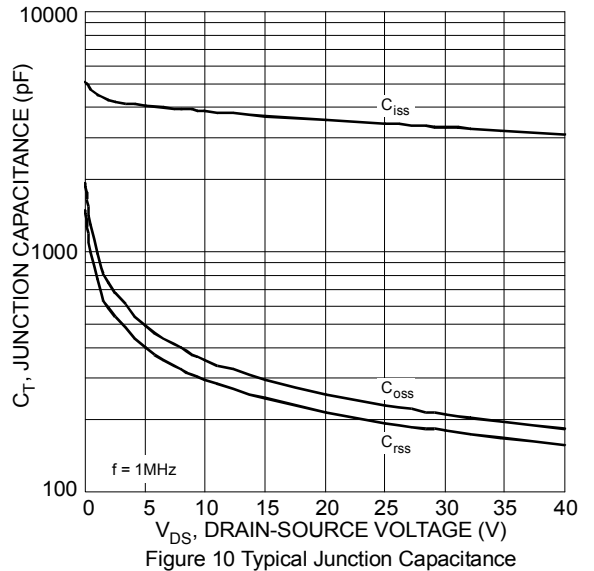
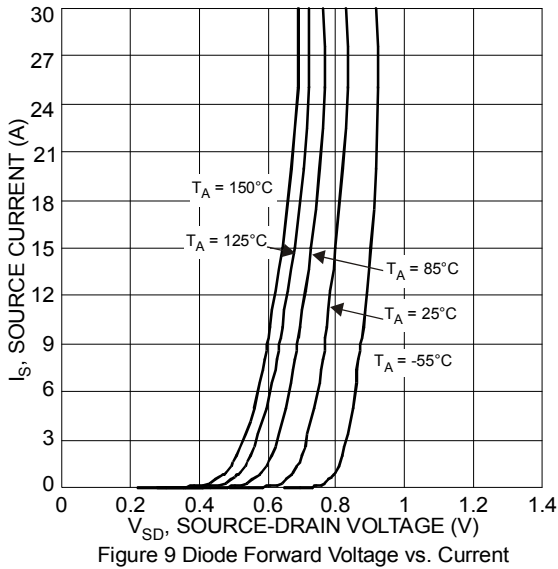
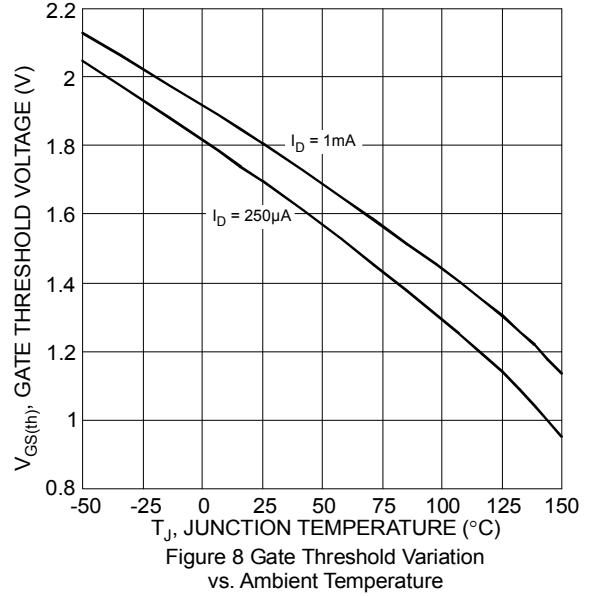
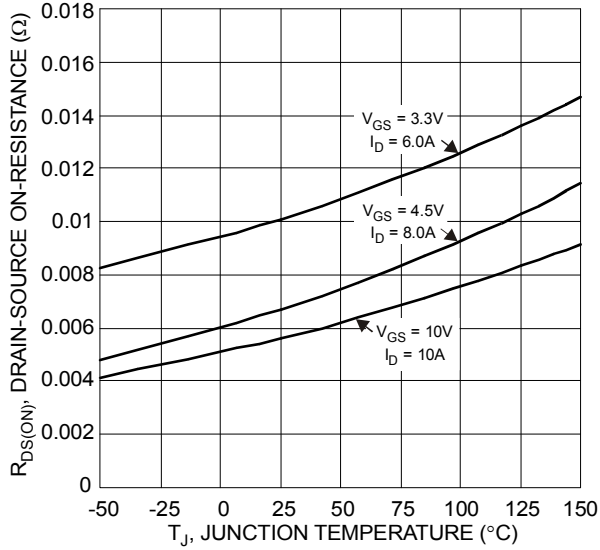
| Characteristic                                   |              | Symbol                            | Value       | Units |
|--------------------------------------------------|--------------|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 5)                 |              | P <sub>D</sub>                    | 1.0         | W     |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady state | R <sub>θJA</sub>                  | 119         | °C/W  |
|                                                  | t < 10s      |                                   | 66          |       |
| Total Power Dissipation (Note 6)                 |              | P <sub>D</sub>                    | 2.3         | W     |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady state | R <sub>θJA</sub>                  | 53          | °C/W  |
|                                                  | t < 10s      |                                   | 30          |       |
| Thermal Resistance, Junction to Case (Note 6)    |              | R <sub>θJC</sub>                  | 6.1         |       |
| Operating and Storage Temperature Range          |              | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C    |

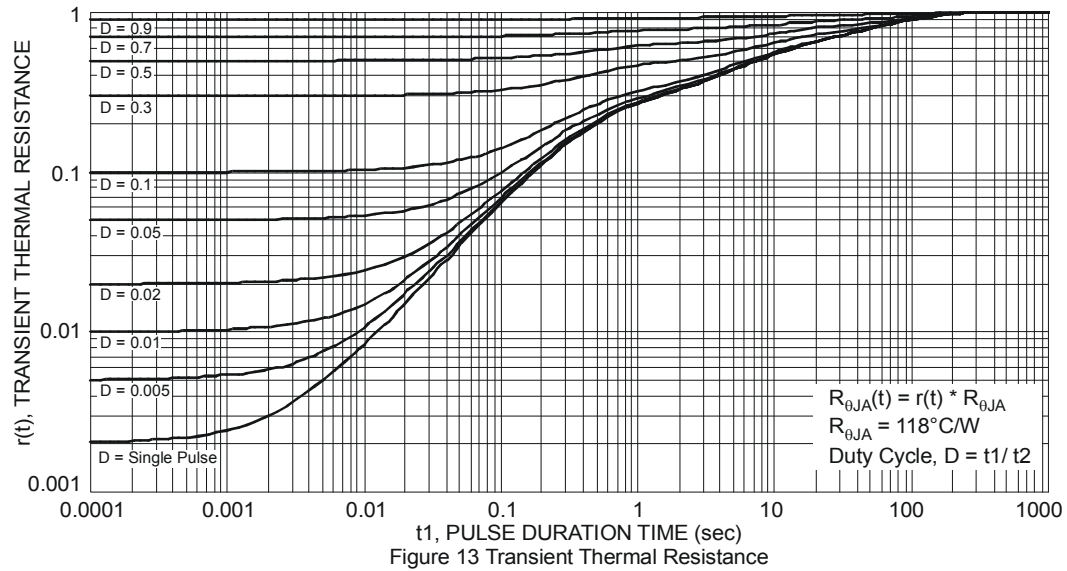
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                         | Symbol              | Min | Typ  | Max  | Unit | Test Condition                                                                          |
|--------------------------------------------------------|---------------------|-----|------|------|------|-----------------------------------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 7)</b>                    |                     |     |      |      |      |                                                                                         |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | 40  | —    | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA                                            |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | —   | —    | 1    | µA   | V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V                                             |
| Gate-Source Leakage                                    | I <sub>GSS</sub>    | —   | —    | ±100 | nA   | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V                                            |
| <b>ON CHARACTERISTICS (Note 7)</b>                     |                     |     |      |      |      |                                                                                         |
| Gate Threshold Voltage                                 | V <sub>GS(th)</sub> | 1   | —    | 3    | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA                              |
| Static Drain-Source On-Resistance                      | R <sub>DS(on)</sub> | —   | 5.5  | 7.5  | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A                                             |
|                                                        |                     | —   | 7    | 10   |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8A                                             |
|                                                        |                     | —   | —    | 20   |      | V <sub>GS</sub> = 3.3V, I <sub>D</sub> = 6A                                             |
| Diode Forward Voltage                                  | V <sub>SD</sub>     | —   | 0.7  | 1.1  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A                                               |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b>                |                     |     |      |      |      |                                                                                         |
| Input Capacitance                                      | C <sub>iss</sub>    | —   | 3537 | —    | pF   | V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz                                   |
| Output Capacitance                                     | C <sub>oss</sub>    | —   | 257  | —    | pF   |                                                                                         |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>    | —   | 215  | —    | pF   |                                                                                         |
| Gate Resistance                                        | R <sub>g</sub>      | —   | 0.9  | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz                                    |
| Total Gate Charge (V <sub>GS</sub> = 4.5V)             | Q <sub>g</sub>      | —   | 34   | —    | nC   | V <sub>DS</sub> = 20V, I <sub>D</sub> = 10A                                             |
| Total Gate Charge (V <sub>GS</sub> = 10V)              | Q <sub>g</sub>      | —   | 74   | —    | nC   |                                                                                         |
| Gate-Source Charge                                     | Q <sub>gs</sub>     | —   | 10.2 | —    | nC   |                                                                                         |
| Gate-Drain Charge                                      | Q <sub>gd</sub>     | —   | 12.5 | —    | nC   |                                                                                         |
| Turn-On Delay Time                                     | t <sub>D(on)</sub>  | —   | 8.2  | —    | ns   | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 20V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 10A |
| Turn-On Rise Time                                      | t <sub>r</sub>      | —   | 14.1 | —    | ns   |                                                                                         |
| Turn-Off Delay Time                                    | t <sub>D(off)</sub> | —   | 69.7 | —    | ns   |                                                                                         |
| Turn-Off Fall Time                                     | t <sub>f</sub>      | —   | 24.4 | —    | ns   |                                                                                         |
| Body Diode Reverse Recovery Time                       | t <sub>rr</sub>     | —   | 18.5 | —    | nS   | I <sub>F</sub> = 10A, di/dt = 100A/µs                                                   |
| Body Diode Reverse Recovery Charge                     | Q <sub>rr</sub>     | —   | 12.0 | —    | nC   |                                                                                         |

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

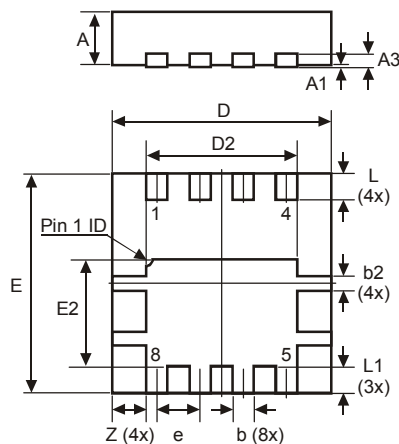






## Package Outline Dimensions

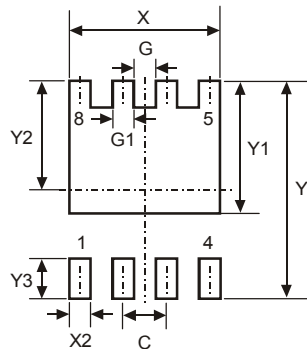
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| POWERDI® 3333-8      |      |      |       |
|----------------------|------|------|-------|
| Dim                  | Min  | Max  | Typ   |
| D                    | 3.25 | 3.35 | 3.30  |
| E                    | 3.25 | 3.35 | 3.30  |
| D2                   | 2.22 | 2.32 | 2.27  |
| E2                   | 1.56 | 1.66 | 1.61  |
| A                    | 0.75 | 0.85 | 0.80  |
| A1                   | 0    | 0.05 | 0.02  |
| A3                   | —    | —    | 0.203 |
| b                    | 0.27 | 0.37 | 0.32  |
| b2                   | —    | —    | 0.20  |
| L                    | 0.35 | 0.45 | 0.40  |
| L1                   | —    | —    | 0.39  |
| e                    | —    | —    | 0.65  |
| Z                    | —    | —    | 0.515 |
| All Dimensions in mm |      |      |       |

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.650         |
| G          | 0.230         |
| G1         | 0.420         |
| Y          | 3.700         |
| Y1         | 2.250         |
| Y2         | 1.850         |
| Y3         | 0.700         |
| X          | 2.370         |
| X2         | 0.420         |

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